AM / FM - PLL

Description

The U4289BM is an integrated circuit in BICMOS technology for frequency synthesizers. It performs all the functions of a PLL radio tuning system and is controlled

by an I^2C bus. The device is designed for all frequency synthesizer applications in radio receivers, as well as RDS (**R**adio **D**ata System) applications.

Features

- Reference oscillator up to 15 MHz
- Two programmable 16 bit dividers adjustable from 2 to 65535
- High signal/noise ratio

- Fine tuning steps: AM ≥ 1 kHz FM ≥ 2 kHz
- Few external component required due to integrated loop-push-pull stage for AM/FM

Ordering and Package Information

Extended Type Number	Package	Remarks
U4289BM-AFP	SO16 plastic	
U4289BM-AFPG3	SO16 plastic	Taping according to IEC-286-3

Block Diagram

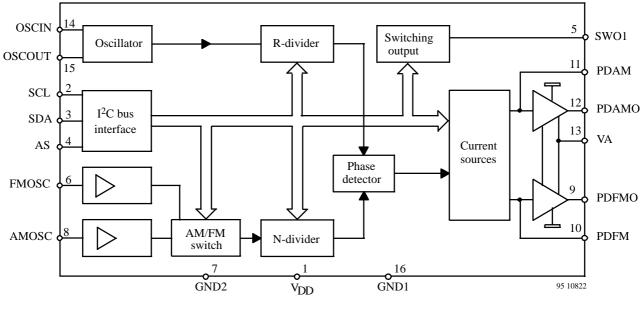
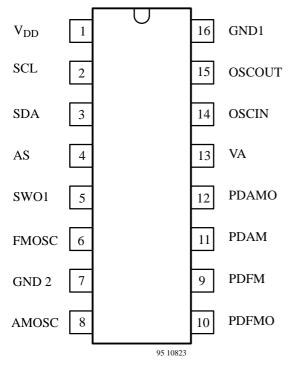


Figure 1.

U4289BM

Pin Description



Pin	Symbol	Function
1	V _{DD}	Supply voltage
2	SCL	I ² C bus clock
3	SDA	I ² C bus data
4	AS	Address selection
5	SWO1	Switching output
6	FMOSC	FM oscillator input
7	GND 2	Ground 2 (analogue)
8	AMOSC	AM oscillator input
9	PDFMO	FM analogue output
10	PDFM	FM current output
11	PDAM	AM current output
12	PDAMO	AM analogue output
13	VA	Analogue supply voltage
14	OSCIN	Oscillator input
15	OSCOUT	Oscillator output
16	GND1	Ground 1 (digital)

Functional Description

The U4289BM is controlled via the 2-wire I^2C bus. For programming there are one module address byte, two subaddress bytes and five data bytes.

The module address contains a programmable address bit A 1 which with address select input AS (Pin 4) makes it possible to operate two U4289BM in one system. If bit A 1 is identical with the status of the address select input AS, the chip is selected .

The subaddress determines which one of the data bytes is transmitted first. If subaddress of R-divider is transmitted, the sequence of the next data bytes is DB 0 (Status), DB 1 and DB 2.

If subaddress of N-divider is transmitted, the sequence of the next data bytes is DB 3 and DB 4. The bit organisation

of the module address, subaddress and 5 data bytes are shown in figure 2.

Each transmission on the I^2C bus begins with the "START"- condition and has to be ended by the "STOP"- condition (see figure 3).

The integrated circuit U4289BM has two separate inputs for AM and FM oscillator. Pre-amplified AM and FM signals are fed to the 16 bit N-divider via AM/FM switch. AM/FM switch is controlled by software. Tuning steps can be selected by 16 bit R-divider. Further there is a digital memory phase detector. There are two separate current sources for AM and FM amplifier (charge pump) as given in electrical characterisitics. It allows independent adjustment of gain, whereby providing high current for high speed tuning and low current for stable tuning.



Bit Organization

	MSB							LSB
Module address	1	1	0	0	1	0	0/1	0
	A7	A6	A5	A4	A3	A2	A1	A0
Subaddress (R-divider)	X	Х	X	0	0	1	X	X
Subaddress (N-divider)	X	Х	X	X	1	1	X	X
	MSB							LSB
Data byte 0 (Status)	SWO1				AM/	PD	PD	PD
	D7	DC	D5	D4	FM	ANA	POL	CUR
	D7	D6	D5	D4	D3	D2	D1	D0
Data byte 1	215			R-di	vider			28
Data byte 2	27			R-di	vider			20
Data byte 3	2 ¹⁵			N-di	vider			28
Data byte 4	27			N-di	vider			20

	LOW HIGH		
AM/FM	FM-operation	AM-operation	
PD – ANA	PD analogue	TEST	
PD – POL	Negative polarity	Positive polarity	
PD – CUR	Output current 2	Output current 1	

Figure 2.

Transmission Protocol

	MSB	LSB										
S	Addı	10	А	Subaddress	А	Data 0	А	Data 1	А	Data 2	А	Р
	A/	A0		R-divider								

	MSB	LSB								
S	Addı	ress	А	Subaddress	А	Data 3	А	Data 4	A	Р
	A7	A0		N-divider				А		

S = Start P = Stop A = Acknowledge

Figure 3.

Absolute Maximum Ratings

Para	ameters	Symbol	Value	Unit
Supply voltage	Pin 1	V _{DD}	-0.3 to +6	V
Input voltage	Pins 2, 3, 4, 6, 8, 14 and 15	VI	-0.3 to V _{DD} + 0.3	V
Output current	Pins 3 and 5	I _O	-1 to +5	mA
Output drain voltage	Pin 5	V _{OD}	15	V
Analogue supply voltage with 220 Ω seriell resistance	Pin 13 e 2 minutes ¹⁾	V _A V _A	6 to 15 24	V V
Output current	Pins 9 and 12	I _{AO}	-1 to +20	mA
Ambient temperature range		T _{amb}	-30 to +85	°C
Storage temperature range		T _{stg}	-40 to +125	°C
Junction temperature		Tj	125	°C
Electrostatic handling (mod method 3015.7: all supply p		$\pm V_{ESD}$	1000	V

1) corresponding our application circuit (page 7)

Thermal Resistance

Parameters	Symbol	Value	Unit
Junction ambient	R _{thJA}	160	K/W

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Electrical Characteristics

$V_{DD} = 5 V, V_A =$	10 V, T _{amb} =	25°C, unless	otherwise	specified
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Parameters	Test condi	tions / Pin	Symbol	Min.	Тур.	Max.	Unit
Supply voltage		Pin 1	V _{DD}	4.5	5.0	5.5	V
Quiescent supply current	AM-mode	Pin 1	I _{DD}		4.0	7.0	mA
	FM-mode		00		4.0	7.0	
FM input sensitivity, R _G =	50 Ω FMOSC	, ,					
$f_i = 70$ to 120 MHz		Pin 6	V _{SFM}	40			mV _{rms}
$f_i = 160 \text{ MHz}$		Pin 6	V _{SFM}	150			mV _{rms}
AM input sensitivity, R _G =	= 50 Ω AMOSO	2					
$f_i = 0.6$ to 35 MHz		Pin 8	V _{SAM}	40			mV _{rms}
Oscillator input sensitivity	$R_{\rm G} = 50 \Omega \rm OS$	CIN					
$f_i = 0.1$ to 15 MHz		Pin 14	V _{SOSC}	100			mV _{rms}
Phase detector PDFM			5656				IIII5
Output current 1		Pin 10	± I _{PDFM}	1600	2000	2400	μA
Output current 2		Pin 10	$\pm I_{PDFM}$	400	500	600	μA
Leakage current		Pin 10	$\pm I_{PDFML}$			20	nA
Phase detector PDAM							
Output current 1		Pin 11	± I _{PDAM}	160	200	240	μΑ
Output current 2		Pin 11	$\pm I_{PDAM}$	40	50	60	μA
Leakage current		Pin 11	$\pm I_{PDAML}$			20	nA
Analogue output PDFMO	, PDAMO						
Saturation voltage	Pi	ins 9 and 12					
LOW	I = 15 mA		V _{satL}		200	400	mV
HIGH			V _{satH}	9.5	9.95		V
I ² C bus SCL, SDA, AS	-				1	1	1
Input voltage	Pi	ins 2, 3 and 4	V _{iBUS}				
HIGH				3.0		V _{DD}	V
LOW		D: 0		0		1.5	V
Output voltage Acknowledge LOW	$I_{m} = 2 m \Lambda$	Pin 3	V.			0.4	v
Clock frequency	$I_{SDA} = 3 \text{ mA}$	Pin 2	V _O			100	kHz
Rise time SDA, SCL		Pins 2 and 3	f _{SCL}			100	
			t _r			-	μs
Fall time SDA, SCL		Pins 2 and 3	t _f			300	ns
Period of SCL HIGH	HIGH	Pin 2	t	4.0			
LOW	LOW		t _H t _L	4.0 4.7			μs μs
Setup time	Lon		<u> </u>	1.7			μι
Start condition			tom	4.7			μs
Data			t _{sSTA} t _{sDAT}	250			ns
Stop condition			t _{sSTOP}	4.7			μs
Time space ¹⁾			35101				, ···
-			t _{wSTA}	4.7			μs
Hold time					-	1	1
Start condition			t _{hSTA}	4.0			μs
DATA			t _{hDAT}	0			μs

¹⁾ This is a space of time where the bus must be free from data transmission and before a new transmission can be started.

U4289BM



Bus Timing

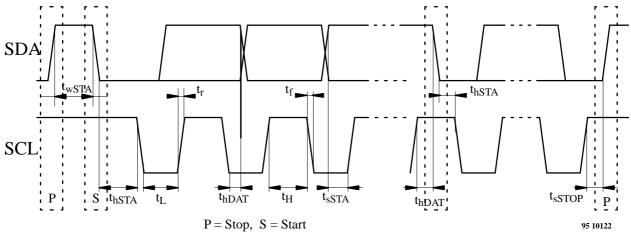


Figure 4.

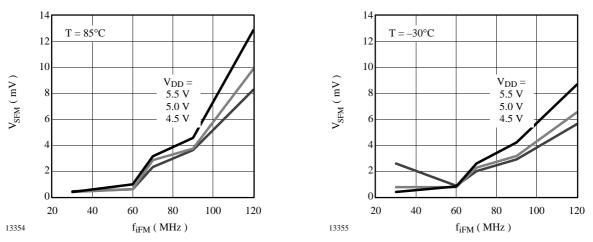


Figure 5. FM input sensitivity



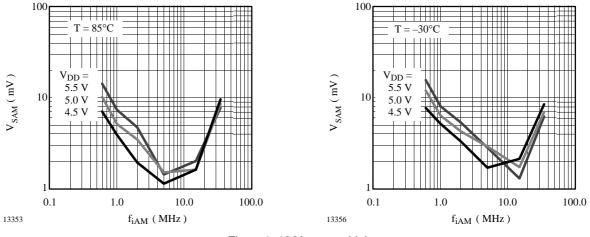
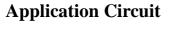


Figure 6. AM input sensitivity



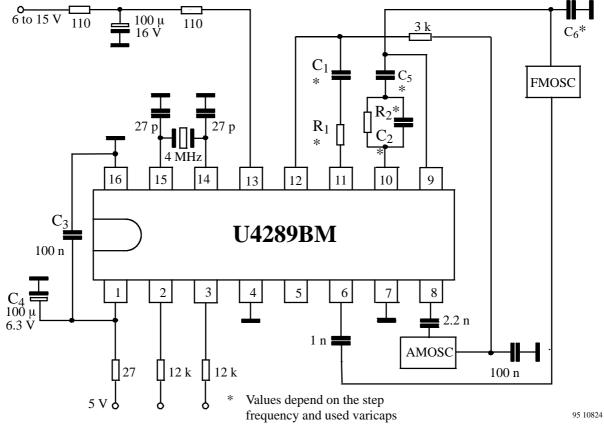


Figure 7.

Recommendations for Applications

- C₃ = 100 nF should be very close to Pin 1 (V_{DD}) and Pin 16 (GND 1)
- GND 2 (Pin 7 analog ground) and GND 1 (Pin 16 digital ground) must be connected according to figure 8

PCB-Layout

- 4 MHz crystal must be very close to Pin 14 and Pin 15
- Components of the charge pump (C₁/R₁ for AM and C₂/R₂ for FM) should be very close to Pin 11 with respect to Pin 10.

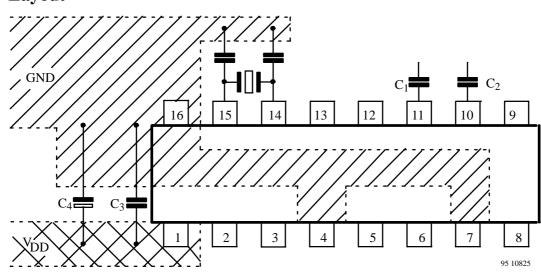


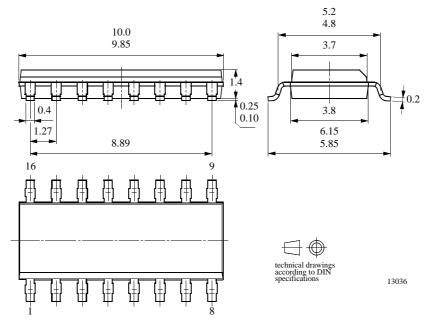
Figure 8.



Package Information

Package SO16

Dimensions in mm



Ozone Depleting Substances Policy Statement

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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